

<b>Notice of References Cited</b>	Application/Control No. 10/586,810		Applicant(s)/Patent Under Reexamination MEUNIER-BEILLARD ET AL.	
	Examiner JOHN DOYLE		Art Unit 2891	Page 1 of 1

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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